Renesas Electronics America Inc - M30627FHPGP#U5C Datasheet

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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Not For New Designs
Core Processor	M16C/60
Core Size	16-Bit
Speed	24MHz
Connectivity	I²C, IEBus, UART/USART
Peripherals	DMA, WDT
Number of I/O	111
Program Memory Size	384KB (384K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	31K x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	A/D 26x10b; D/A 2x8b
Oscillator Type	Internal
Operating Temperature	-20°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	128-LQFP
Supplier Device Package	128-LFQFP (14x20)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/m30627fhpgp-u5c

1. Overview

The M16C/62P Group (M16C/62P, M16C/62PT) of single-chip microcomputers are built using the high performance silicon gate CMOS process using a M16C/60 Series CPU core and are packaged in a 80-pin, 100-pin and 128-pin plastic molded QFP. These single-chip microcomputers operate using sophisticated instructions featuring a high level of instruction efficiency. With 1M bytes of address space, they are capable of executing instructions at high speed. In addition, this microcomputer contains a multiplier and DMAC which combined with fast instruction processing capability, makes it suitable for control of various OA, communication, and industrial equipment which requires high-speed arithmetic/logic operations.

1.1 Applications

Audio, cameras, television, home appliance, office/communications/portable/industrial equipment, automobile, etc.

Specifications written in this manual are believed to be accurate, but are not guaranteed to be entirely free of error. Specifications in this manual may be changed for functional or performance improvements. Please make sure your manual is the latest edition.

Table 1.2 Performance Outline of M16C/62P Group (M16C/62P, M16C/62PT)(100-pin version)

	Item	Performance	
		M16C/62P	M16C/62PT(4)
CPU	Number of Basic Instructions	91 instructions	
	Minimum Instruction Execution Time	41.7ns(f(BCLK)=24MHz, VCC1=3.3 to 5.5V) 100ns(f(BCLK)=10MHz, VCC1=2.7 to 5.5V)	41.7ns(f(BCLK)=24MHz, VCC1=4.0 to 5.5V)
	Operating Mode	Single-chip, memory expansion and microprocessor mode	Single-chip
	Address Space	1 Mbyte (Available to 4 Mbytes by memory space expansion function)	1 Mbyte
	Memory Capacity	See **Table 1.4 to 1.7 Product List**	
Peripheral Function	Port	Input/Output : 87 pins, Input : 1 pin	
	Multifunction Timer	Timer A : 16 bits x 5 channels, Timer B : 16 bits x 6 channels, Three phase motor control circuit	
	Serial Interface	3 channels Clock synchronous, UART, I2C bus(1), IEBus(2) 2 channels Clock synchronous	
	A/D Converter	10-bit A/D converter: 1 circuit, 26 channels	
	D/A Converter	8 bits x 2 channels	
	DMAC	2 channels	
	CRC Calculation Circuit	CCITT-CRC	
	Watchdog Timer	15 bits x 1 channel (with prescaler)	
	Interrupt	Internal: 29 sources, External: 8 sources, Software: 4 sources, Priority level: 7 levels	
	Clock Generation Circuit	4 circuits Main clock generation circuit (*), Subclock generation circuit (*), On-chip oscillator, PLL synthesizer (*)Equipped with a built-in feedback resistor.	
	Oscillation Stop Detection Function	Stop detection of main clock oscillation, re-oscillation detection function	
	Voltage Detection Circuit	Available (option (5))	Absent
Electric Characteristics	Supply Voltage	VCC1=3.0 to 5.5 V, VCC2=2.7V to VCC1 (f(BCLK=24MHz) VCC1=2.7 to 5.5 V, VCC2=2.7V to VCC1 (f(BCLK=10MHz)	VCC1=VCC2=4.0 to 5.5V (f(BCLK=24MHz)
	Power Consumption	14 mA (VCC1=VCC2=5V, f(BCLK)=24MHz) 8 mA (VCC1=VCC2=3V, f(BCLK)=10MHz) 1.8µA (VCC1=VCC2=3V, f(XCIN)=32kHz, wait mode) 0.7µA (VCC1=VCC2=3V, stop mode)	14 mA (VCC1=VCC2=5V, f(BCLK)=24MHz) 2.0µA (VCC1=VCC2=5V, f(XCIN)=32kHz, wait mode) 0.8µA (VCC1=VCC2=5V, stop mode)
Flash memory version	Program/Erase Supply Voltage	3.3±0.3 V or 5.0±0.5 V	5.0±0.5 V
	Program and Erase Endurance	100 times (all area) or 1,000 times (user ROM area without block A and block 1) / 10,000 times (block A, block 1) (3)	
Operating Ambient Temperature		-20 to 85°C, -40 to 85°C (3)	T version : -40 to 85°C V version : -40 to 125°C
Package		100-pin plastic mold QFP, LQFP	

NOTES:
1. I2C bus is a registered trademark of Koninklijke Philips Electronics N. V.
2. IEBus is a registered trademark of NEC Electronics Corporation.
3. See **Table 1.8 and 1.9 Product Code** for the program and erase endurance, and operating ambient temperature.
   In addition 1,000 times/10,000 times are under development as of Jul., 2005. Please inquire about a release schedule.
4. Use the M16C/62PT on VCC1=VCC2
5. All options are on request basis.

Table 1.5 Product List (2) (M16C/62P) As of Dec. 2005

Type No.	ROM Capacity	RAM Capacity	Package Type (1)	Remarks
M30622MHP-XXXFP	384 Kbytes	16 Kbytes	PRQP0100JB-A	Mask ROM version
M30622MHP-XXXGP			PLQP0100KB-A	
M30623MHP-XXXGP			PLQP0128KB-A	
M30624MHP-XXXFP		24 Kbytes	PRQP0100JB-A	
M30624MHP-XXXGP			PLQP0100KB-A	
M30625MHP-XXXGP			PLQP0128KB-A	
M30626MHP-XXXFP		31 Kbytes	PRQP0100JB-A	
M30626MHP-XXXGP			PLQP0100KB-A	
M30627MHP-XXXGP			PLQP0128KB-A	
M30626MJP-XXXFP (D)	512 Kbytes	31 Kbytes	PRQP0100JB-A	
M30626MJP-XXXGP (D)			PLQP0100KB-A	
M30627MJP-XXXGP (D)			PLQP0128KB-A	
M30622F8PFP	64K+4 Kbytes	4 Kbytes	PRQP0100JB-A	Flash memory version (2)
M30622F8PGP			PLQP0100KB-A	
M30623F8PGP			PRQP0080JA-A	
M30620FCPFP	128K+4 Kbytes	10 Kbytes	PRQP0100JB-A	
M30620FCPGP			PLQP0100KB-A	
M30621FCPGP			PRQP0080JA-A	
M3062LFGPFP(3) (D)	256K+4 Kbytes	20 Kbytes	PRQP0100JB-A	
M3062LFGPGP(3) (D)			PLQP0100KB-A	
M30625FGPGP			PLQP0128KB-A	
M30626FHPFP	384K+4 Kbytes	31 Kbytes	PRQP0100JB-A	
M30626FHPGP			PLQP0100KB-A	
M30627FHPGP			PLQP0128KB-A	
M30626FJPFP	512K+4 Kbytes	31 Kbytes	PRQP0100JB-A	
M30626FJPGP			PLQP0100KB-A	
M30627FJPGP			PLQP0128KB-A	
M30622SPFP	–	4 Kbytes	PRQP0100JB-A	ROM-less version
M30622SPGP			PLQP0100KB-A	
M30620SPFP		10 Kbytes	PRQP0100JB-A	
M30620SPGP			PLQP0100KB-A	
M30624SPFP (D)	–	20 Kbytes	PRQP0100JB-A	
M30624SPGP (D)			PLQP0100KB-A	
M30626SPFP (D)		31 Kbytes	PRQP0100JB-A	
M30626SPGP (D)			PLQP0100KB-A	

(D): Under development

NOTES:

1. The old package type numbers of each package type are as follows.
   PLQP0128KB-A : 128P6Q-A,
   PRQP0100JB-A : 100P6S-A,
   PLQP0100KB-A : 100P6Q-A,
   PRQP0080JA-A : 80P6S-A
2. In the flash memory version, there is 4K bytes area (block A).
3. Please use M3062LFGPFP and M3062LFGPGP for your new system instead of M30624FGPFP and M30624FGPGP. The M16C/62P Group (M16C/62P, M16C/62PT) hardware manual is still good for M30624FGPFP and M30624FGPGP.

M30624FGPFP	256K+4 Kbytes	20 Kbytes	PRQP0100JB-A	Flash memory version
M30624FGPGP			PLQP0100KB-A	

Table 1.8 Product Code of Flash Memory version and ROMless version for M16C/62P

	Product Code	Package	Internal ROM (User ROM Area Without Block A, Block 1)		Internal ROM (Block A, Block 1)		Operating Ambient Temperature
			Program and Erase Endurance	Temperature Range	Program and Erase Endurance	Temperature Range	
Flash memory Version	D3	Lead-included	100	0°C to 60°C	100	0°C to 60°C	-40°C to 85°C
	D5						-20°C to 85°C
	D7		1,000		10,000	-40°C to 85°C	-40°C to 85°C
	D9					-20°C to 85°C	-20°C to 85°C
	U3	Lead-free	100		100	0°C to 60°C	-40°C to 85°C
	U5						-20°C to 85°C
	U7		1,000		10,000	-40°C to 85°C	-40°C to 85°C
	U9					-20°C to 85°C	-20°C to 85°C
ROM-less version	D3	Lead-included	–	–	–	–	-40°C to 85°C
	D5						-20°C to 85°C
	U3	Lead-free	–	–	–	–	-40°C to 85°C
	U5						-20°C to 85°C

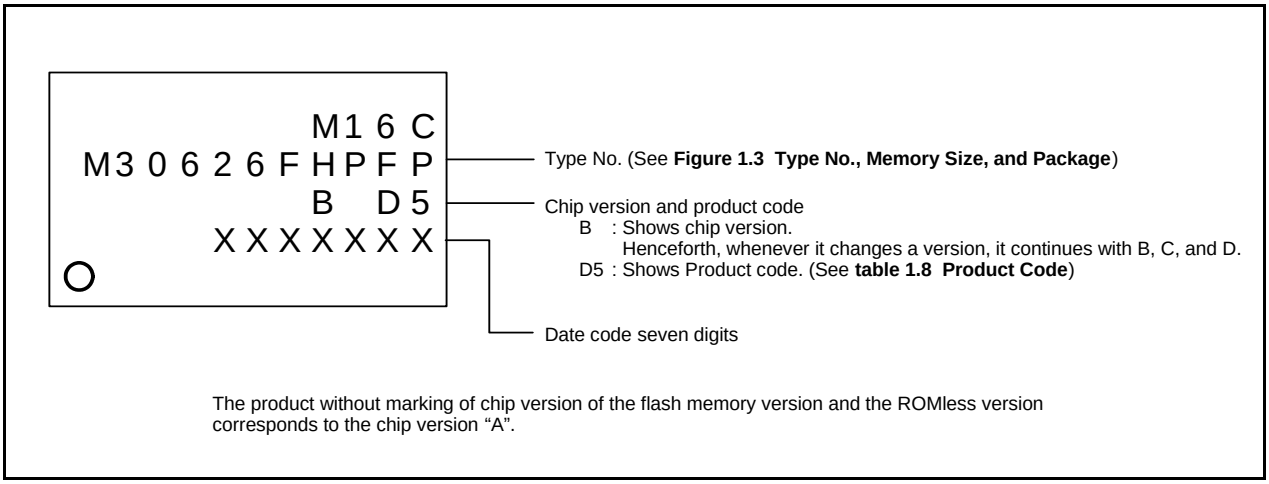


Figure 1.4 Marking Diagram of Flash Memory version and ROM-less version for M16C/62P (Top View)

Table 1.12 Pin Characteristics for 128-Pin Package (3)

Pin No.	Control Pin	Port	Interrupt Pin	Timer Pin	UART Pin	Analog Pin	Bus Control Pin
101		P1_2					D10
102		P1_1					D9
103		P1_0					D8
104		P0_7				AN0_7	D7
105		P0_6				AN0_6	D6
106		P0_5				AN0_5	D5
107		P0_4				AN0_4	D4
108		P0_3				AN0_3	D3
109		P0_2				AN0_2	D2
110		P0_1				AN0_1	D1
111		P0_0				AN0_0	D0
112		P11_7					
113		P11_6					
114		P11_5					
115		P11_4					
116		P11_3					
117		P11_2					
118		P11_1					
119		P11_0					
120		P10_7	$\overline{KI3}$			AN7	
121		P10_6	$\overline{KI2}$			AN6	
122		P10_5	$\overline{KI1}$			AN5	
123		P10_4	$\overline{KI0}$			AN4	
124		P10_3				AN3	
125		P10_2				AN2	
126		P10_1				AN1	
127	AVSS						
128		P10_0				AN0	

Table 1.13 Pin Characteristics for 100-Pin Package (1)

Pin No.		Control Pin	Port	Interrupt Pin	Timer Pin	UART Pin	Analog Pin	Bus Control Pin
FP	GP							
1	99		P9_6			SOUT4	ANEX1	
2	100		P9_5			CLK4	ANEX0	
3	1		P9_4		TB4IN		DA1	
4	2		P9_3		TB3IN		DA0	
5	3		P9_2		TB2IN	SOUT3		
6	4		P9_1		TB1IN	SIN3		
7	5		P9_0		TB0IN	CLK3		
8	6	BYTE						
9	7	CNVSS						
10	8	XCIN	P8_7					
11	9	XCOUT	P8_6					
12	10	$\overline{\text{RESET}}$						
13	11	XOUT						
14	12	VSS						
15	13	XIN						
16	14	VCC1						
17	15		P8_5	$\overline{\text{NMI}}$				
18	16		P8_4	$\overline{\text{INT2}}$	ZP			
19	17		P8_3	$\overline{\text{INT1}}$				
20	18		P8_2	$\overline{\text{INT0}}$				
21	19		P8_1		TA4IN/$\overline{\text{U}}$			
22	20		P8_0		TA4OUT/U			
23	21		P7_7		TA3IN			
24	22		P7_6		TA3OUT			
25	23		P7_5		TA2IN/$\overline{\text{W}}$			
26	24		P7_4		TA2OUT/W			
27	25		P7_3		TA1IN/$\overline{\text{V}}$	$\overline{\text{CTS2}}$/$\overline{\text{RTS2}}$		
28	26		P7_2		TA1OUT/V	CLK2		
29	27		P7_1		TA0IN/TB5IN	RXD2/SCL2		
30	28		P7_0		TA0OUT	TXD2/SDA2		
31	29		P6_7			TXD1/SDA1		
32	30		P6_6			RXD1/SCL1		
33	31		P6_5			CLK1		
34	32		P6_4			$\overline{\text{CTS1}}$/$\overline{\text{RTS1}}$/$\overline{\text{CTS0}}$/CLKS1		
35	33		P6_3			TXD0/SDA0		
36	34		P6_2			RXD0/SCL0		
37	35		P6_1			CLK0		
38	36		P6_0			$\overline{\text{CTS0}}$/$\overline{\text{RTS0}}$		
39	37		P5_7					$\overline{\text{RDY}}$/CLKOUT
40	38		P5_6					ALE
41	39		P5_5					$\overline{\text{HOLD}}$
42	40		P5_4					$\overline{\text{HLAD}}$
43	41		P5_3					BCLK
44	42		P5_2					$\overline{\text{RD}}$
45	43		P5_1					$\overline{\text{WRH}}$/$\overline{\text{BHE}}$
46	44		P5_0					$\overline{\text{WRL}}$/$\overline{\text{WR}}$
47	45		P4_7					$\overline{\text{CS3}}$
48	46		P4_6					$\overline{\text{CS2}}$
49	47		P4_5					$\overline{\text{CS1}}$
50	48		P4_4					$\overline{\text{CS0}}$

Table 5.2 Recommended Operating Conditions (1) (1)

Symbol	Parameter		Standard			Unit
			Min.	Typ.	Max.	
V_{CC1}, V_{CC2}	Supply Voltage ($V_{CC1} \geq V_{CC2}$)		2.7	5.0	5.5	V
AVcc	Analog Supply Voltage			V_{CC1}		V
Vss	Supply Voltage			0		V
AVss	Analog Supply Voltage			0		V
V_{IH}	HIGH Input Voltage	P3_1 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P12_0 to P12_7, P13_0 to P13_7	0.8V_{CC2}		V_{CC2}	V
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 (during single-chip mode)	0.8V_{CC2}		V_{CC2}	V
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 (data input during memory expansion and microprocessor mode)	0.5V_{CC2}		V_{CC2}	V
		P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P14_0, P14_1, XIN, $\overline{RESET}$, CNVSS, BYTE	0.8V_{CC1}		V_{CC1}	V
		P7_0, P7_1	0.8V_{CC1}		6.5	V
V_{IL}	LOW Input Voltage	P3_1 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P12_0 to P12_7, P13_0 to P13_7	0		0.2V_{CC2}	V
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 (during single-chip mode)	0		0.2V_{CC2}	V
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 (data input during memory expansion and microprocessor mode)	0		0.16V_{CC2}	V
		P6_0 to P6_7, P7_0 to P7_7, P8_0 to P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P14_0, P14_1, XIN, $\overline{RESET}$, CNVSS, BYTE	0		0.2V_{CC}	V
$I_{OH(peak)}$	HIGH Peak Output Current	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P12_0 to P12_7, P13_0 to P13_7, P14_0, P14_1			–10.0	mA
$I_{OH(avg)}$	HIGH Average Output Current	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P12_0 to P12_7, P13_0 to P13_7, P14_0, P14_1			–5.0	mA
$I_{OL(peak)}$	LOW Peak Output Current	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_0 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P12_0 to P12_7, P13_0 to P13_7, P14_0, P14_1			10.0	mA
$I_{OL(avg)}$	LOW Average Output Current	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_0 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P12_0 to P12_7, P13_0 to P13_7, P14_0, P14_1			5.0	mA

NOTES:

1. Referenced to V_{CC1} = V_{CC2} = 2.7 to 5.5V at T_{opr} = –20 to 85°C / –40 to 85°C unless otherwise specified.
2. The Average Output Current is the mean value within 100ms.
3. The total $I_{OL(peak)}$ for ports P0, P1, P2, P8_6, P8_7, P9, P10, P11, P14_0, and P14_1 must be 80mA max. The total $I_{OL(peak)}$ for ports P3, P4, P5, P6, P7, P8_0 to P8_4, P12, and P13 must be 80mA max. The total $I_{OH(peak)}$ for ports P0, P1, and P2 must be –40mA max. The total $I_{OH(peak)}$ for ports P3, P4, P5, P12, and P13 must be –40mA max. The total $I_{OH(peak)}$ for ports P6, P7, and P8_0 to P8_4 must be –40mA max. The total $I_{OH(peak)}$ for ports P8_6, P8_7, P9, P10, P14_0, and P14_1 must be –40mA max. Set Average Output Current to 1/2 of peak. The total $I_{OH(peak)}$ for ports P8_6, P8_7, P9 , P10, P11, P14_0, and P14_1 must be –40mA max.
   As for 80-pin version, the total $I_{OL(peak)}$ for all ports and $I_{OH(peak)}$ must be 80mA. max. due to one V_{CC} and one V_{SS}.
4. There is no external connections for port P1_0 to P1_7, P4_4 to P4_7, P7_2 to P7_5 and P9_1 in 80-pin version.

Table 5.12 Electrical Characteristics (2) (1)

Symbol	Parameter		Measuring Condition		Standard			Unit
					Min.	Typ.	Max.	
I_{CC}	Power Supply Current (V_{CC1}=V_{CC2}=4.0V to 5.5V)	In single-chip mode, the output pins are open and other pins are V_{SS}	Mask ROM	f(BCLK)=24MHz No division, PLL operation		14	20	mA
				No division, On-chip oscillation		1		mA
			Flash Memory	f(BCLK)=24MHz, No division, PLL operation		18	27	mA
				No division, On-chip oscillation		1.8		mA
			Flash Memory Program	f(BCLK)=10MHz, VCC1=5.0V		15		mA
			Flash Memory Erase	f(BCLK)=10MHz, VCC1=5.0V		25		mA
			Mask ROM	f(XCIN)=32kHz Low power dissipation mode, ROM (3)		25		µA
			Flash Memory	f(BCLK)=32kHz Low power dissipation mode, RAM (3)		25		µA
				f(BCLK)=32kHz Low power dissipation mode, Flash Memory (3)		420		µA
				On-chip oscillation, Wait mode		50		µA
			Mask ROM Flash Memory	f(BCLK)=32kHz Wait mode (2), Oscillation capability High		7.5		µA
				f(BCLK)=32kHz Wait mode (2), Oscillation capability Low		2.0		µA
				Stop mode Topr =25°C		0.8	3.0	µA
I_{det4}	Low Voltage Detection Dissipation Current (4)					0.7	4	µA
I_{det3}	Reset Area Detection Dissipation Current (4)					1.2	8	µA

NOTES:
1. Referenced to V_{CC1}=V_{CC2}=4.2 to 5.5V, V_{SS} = 0V at T_{opr} = –20 to 85°C / –40 to 85°C, f(BCLK)=24MHz unless otherwise specified.
2. With one timer operated using fC32.
3. This indicates the memory in which the program to be executed exists.
4. I_{det} is dissipation current when the following bit is set to “1” (detection circuit enabled).

   I_{det4}: VC27 bit in the VCR2 register

   I_{det3}: VC26 bit in the VCR2 register

$V_{CC1}=V_{CC2}=5V$

Switching Characteristics

(V_{CC1} = V_{CC2} = 5V, V_{SS} = 0V, at T_{opr} = –20 to 85°C / –40 to 85°C unless otherwise specified)

Table 5.27 Memory Expansion and Microprocessor Modes (for setting with no wait)

Symbol	Parameter		Standard		Unit
			Min.	Max.	
td(BCLK-AD)	Address Output Delay Time	See **Figure 5.2**		25	ns
th(BCLK-AD)	Address Output Hold Time (in relation to BCLK)		4		ns
th(RD-AD)	Address Output Hold Time (in relation to RD)		0		ns
th(WR-AD)	Address Output Hold Time (in relation to WR)		(NOTE 2)		ns
td(BCLK-CS)	Chip Select Output Delay Time			25	ns
th(BCLK-CS)	Chip Select Output Hold Time (in relation to BCLK)		4		ns
td(BCLK-ALE)	ALE Signal Output Delay Time			15	ns
th(BCLK-ALE)	ALE Signal Output Hold Time		–4		ns
td(BCLK-RD)	RD Signal Output Delay Time			25	ns
th(BCLK-RD)	RD Signal Output Hold Time		0		ns
td(BCLK-WR)	WR Signal Output Delay Time			25	ns
th(BCLK-WR)	WR Signal Output Hold Time		0		ns
td(BCLK-DB)	Data Output Delay Time (in relation to BCLK)			40	ns
th(BCLK-DB)	Data Output Hold Time (in relation to BCLK) (3)		4		ns
td(DB-WR)	Data Output Delay Time (in relation to WR)		(NOTE 1)		ns
th(WR-DB)	Data Output Hold Time (in relation to WR) (3)		(NOTE 2)		ns
td(BCLK-HLDA)	HLDA Output Delay Time			40	ns

NOTES:

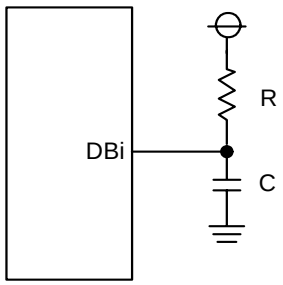
1. Calculated according to the BCLK frequency as follows:

$$\frac{0.5\times10^{9}}{f(BCLK)} - 40[ns]$$ f(BCLK) is 12.5MHz or less.

2. Calculated according to the BCLK frequency as follows:

$$\frac{0.5\times10^{9}}{f(BCLK)} - 10[ns]$$

3. This standard value shows the timing when the output is off, and does not show hold time of data bus.
   Hold time of data bus varies with capacitor volume and pull-up (pull-down) resistance value.
   Hold time of data bus is expressed in
   $t = -CR \times \ln(1 - V_{OL} / V_{CC2})$
   by a circuit of the right figure.
   For example, when $V_{OL} = 0.2V_{CC2}$, C = 30pF, R = 1kΩ, hold time of output "L" level is
   $t = -30pF \times 1k\Omega \times \ln(1 - 0.2V_{CC2} / V_{CC2})$
   = 6.7ns.



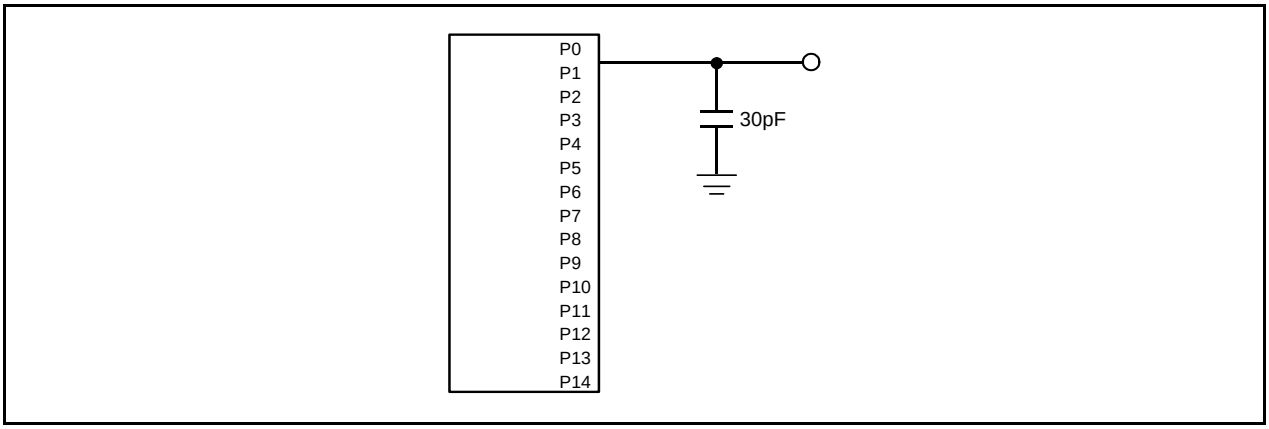
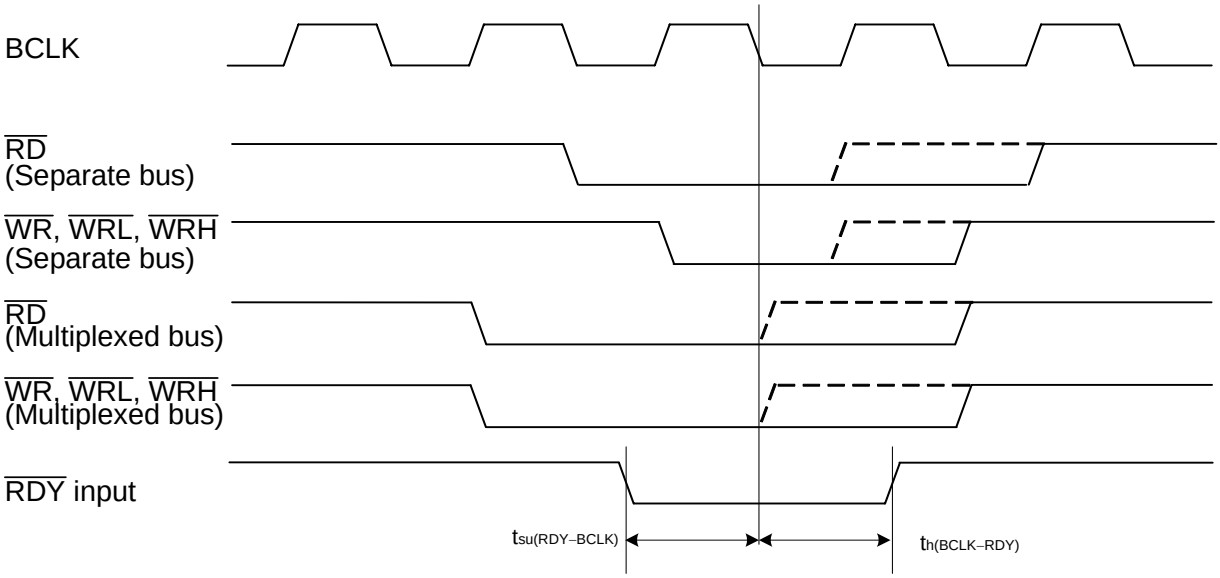


Figure 5.2 Ports P0 to P14 Measurement Circuit

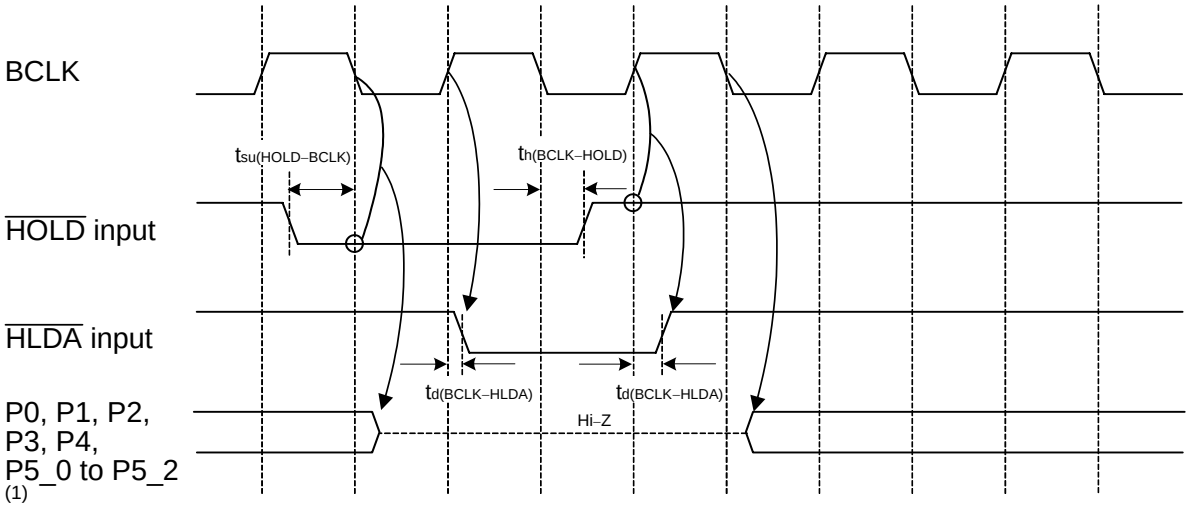
$V_{CC1}=V_{CC2}=5V$

Memory Expansion Mode, Microprocessor Mode

(Effective for setting with wait**)**



(Common to setting with wait and setting without wait**)**



NOTES:

1. These pins are set to high-impedance regardless of the input level of the BYTE pin, PM06 bit in PM0 register and PM11 bit in PM1 register.

· Measuring conditions :
· $V_{CC1}=V_{CC2}=5V$
· Input timing voltage : Determined with $V_{IL}=1.0V$, $V_{IH}=4.0V$
· Output timing voltage : Determined with $V_{OL}=2.5V$, $V_{OH}=2.5V$

Figure 5.5 Timing Diagram (3)

$V_{CC1}=V_{CC2}=3V$

Table 5.30 Electrical Characteristics (1) (1)

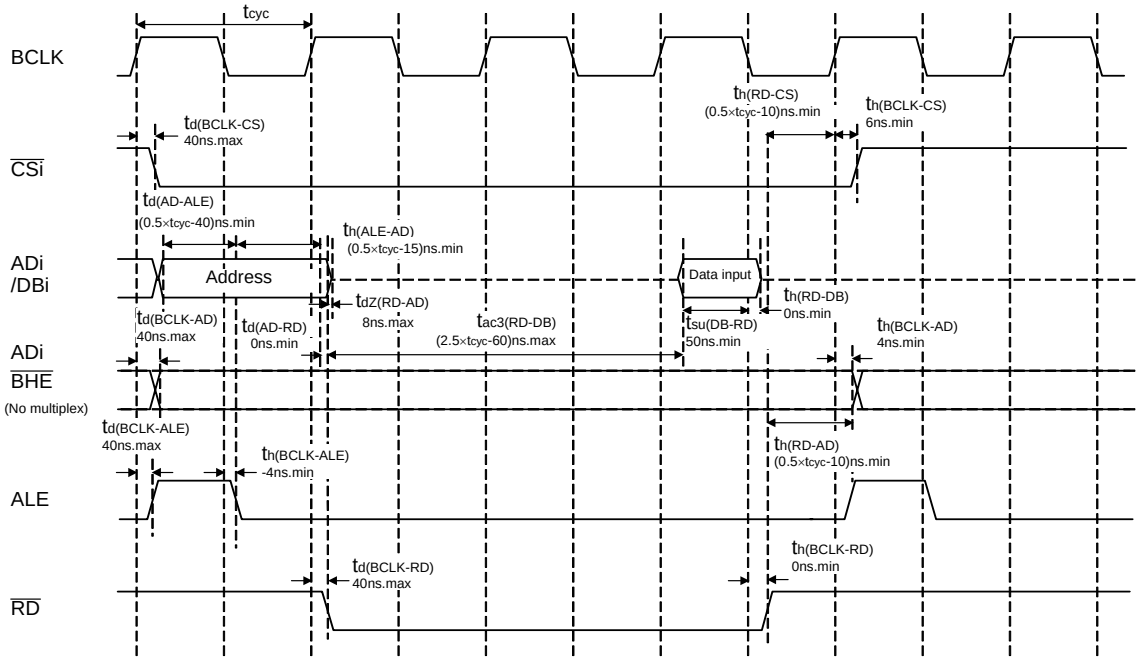
Symbol	Parameter		Measuring Condition	Standard			Unit
				Min.	Typ.	Max.	
V_{OH}	HIGH Output Voltage (3)	P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P14_0, P14_1	I_{OH}=–1mA	V_{CC1}–0.5		V_{CC1}	V
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P12_0 to P12_7, P13_0 to P13_7	I_{OH}=–1mA (2)	V_{CC2}–0.5		V_{CC2}	
V_{OH}	HIGH Output Voltage XOUT	HIGHPOWER	I_{OH}=–0.1mA	V_{CC1}–0.5		V_{CC1}	V
		LOWPOWER	I_{OH}=–50µA	V_{CC1}–0.5		V_{CC1}	
	HIGH Output Voltage XCOUT	HIGHPOWER	With no load applied		2.5		V
		LOWPOWER	With no load applied		1.6		
V_{OL}	LOW Output Voltage (3)	P6_0 to P6_7, P7_0 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P14_0, P14_1	I_{OL}=1mA			0.5	V
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P12_0 to P12_7, P13_0 to P13_7	I_{OL}=1mA (2)			0.5	
V_{OL}	LOW Output Voltage XOUT	HIGHPOWER	I_{OL}=0.1mA			0.5	V
		LOWPOWER	I_{OL}=50µA			0.5	
	LOW Output Voltage XCOUT	HIGHPOWER	With no load applied		0		V
		LOWPOWER	With no load applied		0		
V_{T+}-V_{T-}	Hysteresis	$\overline{HOLD}$, $\overline{RDY}$, TA0IN to TA4IN, $\overline{TB0IN}$ to $\overline{TB5IN}$, $\overline{INT0}$ to $\overline{INT5}$, $\overline{NMI}$, $\overline{ADTRG}$, $\overline{CTS0}$ to $\overline{CTS2}$, CLK0 to CLK4, TA0OUT to TA4OUT, $\overline{KI0}$ to $\overline{KI3}$, RXD0 to RXD2, SCL0 to SCL2, SDA0 to SDA2, SIN3, SIN4		0.2		0.8	V
V_{T+}-V_{T-}	Hysteresis	$\overline{RESET}$		0.2	(0.7)	1.8	V
I_{IH}	HIGH Input Current (3)	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_0 to P7_7, P8_0 to P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P12_0 to P12_7, P13_0 to P13_7, P14_0, P14_1, XIN, $\overline{RESET}$, CNVSS, BYTE	V_I=3V			4.0	µA
I_{IL}	LOW Input Current (3)	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_0 to P7_7, P8_0 to P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P12_0 to P12_7, P13_0 to P13_7, P14_0, P14_1, XIN, $\overline{RESET}$, CNVSS, BYTE	V_I=0V			–4.0	µA
R_{PULLUP}	Pull-Up Resistance (3)	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7,P12_0 to P12_7, P13_0 to P13_7, P14_0, P14_1	V_I=0V	50	100	500	kΩ
R_{fXIN}	Feedback Resistance XIN				3.0		MΩ
R_{fXCIN}	Feedback Resistance XCIN				25		MΩ
V_{RAM}	RAM Retention Voltage		At stop mode	2.0			V

NOTES:
1. Referenced to V_{CC1} = V_{CC2} = 2.7 to 3.3V, V_{SS} = 0V at Topr = –20 to 85°C / –40 to 85°C, f(XIN)=10MHz no wait unless otherwise specified.
2. V_{CC1} for the port P6 to P11 and P14, and V_{CC2} for the port P0 to P5 and P12 to P13
3. There is no external connections for port P1_0 to P1_7, P4_4 to P4_7, P7_2 to P7_5 and P9_1 in 80-pin version.

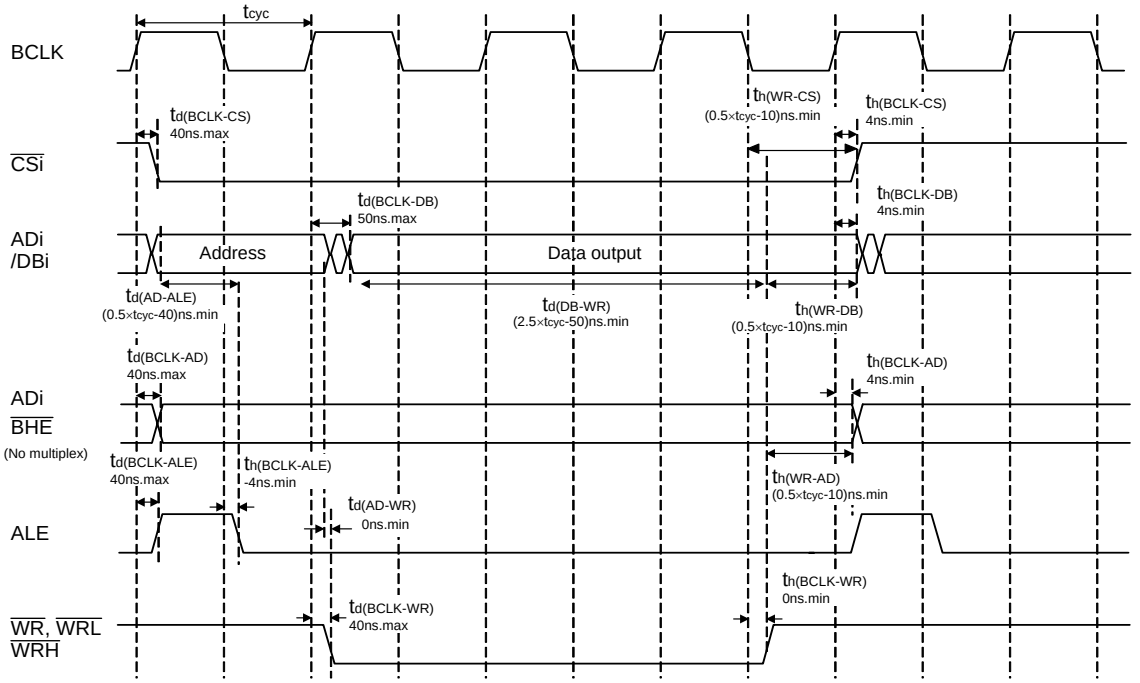
$V_{CC1}=V_{CC2}=3V$

Memory Expansion Mode, Microprocessor Mode
(For 3-wait setting, external area access and multiplex bus selection)

Read timing



Write timing



$$t_{cyc}=\frac{1}{f(BCLK)}$$

Measuring conditions
- $V_{CC1}=V_{CC2}=3V$
- Input timing voltage : $V_{IL}=0.6V$, $V_{IH}=2.4V$
- Output timing voltage : $V_{OL}=1.5V$, $V_{OH}=1.5V$

Figure 5.21 Timing Diagram (9)

5.2 Electrical Characteristics (M16C/62PT)

Table 5.49 Absolute Maximum Ratings

Symbol	Parameter		Condition	Rated Value	Unit
V_{CC1}, V_{CC2}	Supply Voltage		V_{CC1}=V_{CC2}=AVcc	–0.3 to 6.5	V
AVcc	Analog Supply Voltage		V_{CC1}=V_{CC2}=AVcc	–0.3 to 6.5	V
V_I	Input Voltage	$\overline{\text{RESET}}$, CNVSS, BYTE, P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P14_0, P14_1, VREF, XIN		–0.3 to V_{CC1}+0.3 (1)	V
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P12_0 to P12_7, P13_0 to P13_7		–0.3 to V_{CC2}+0.3 (1)	V
		P7_0, P7_1		–0.3 to 6.5	V
V_O	Output Voltage	P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P14_0, P14_1, XOUT		–0.3 to V_{CC1}+0.3 (1)	V
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P12_0 to P12_7, P13_0 to P13_7		–0.3 to V_{CC2}+0.3 (1)	V
		P7_0, P7_1		–0.3 to 6.5	V
P_d	Power Dissipation		–40°C<T_{opr}≤85°C	300	mW
			85°C<T_{opr}≤125°C	200	
T_{opr}	Operating Ambient Temperature	When the Microcomputer is Operating		–40 to 85 / –40 to 125 (2)	°C
		Flash Program Erase		0 to 60	
T_{stg}	Storage Temperature			–65 to 150	°C

NOTES:
1. There is no external connections for port P1_0 to P1_7, P4_4 to P4_7, P7_2 to P7_5 and P9_1 in 80-pin version.
2. T version = –40 to 85 °C, V version= –40 to 125 °C.

Table 5.50 Recommended Operating Conditions (1) (1)

Symbol	Parameter		Standard			Unit
			Min.	Typ.	Max.	
V_{CC1}, V_{CC2}	Supply Voltage (V_{CC1} = V_{CC2})		4.0	5.0	5.5	V
AVcc	Analog Supply Voltage			V_{CC1}		V
Vss	Supply Voltage			0		V
AVss	Analog Supply Voltage			0		V
V_{IH}	HIGH Input Voltage (4)	P3_1 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P12_0 to P12_7, P13_0 to P13_7	0.8V_{CC2}		V_{CC2}	V
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 (during single-chip mode)	0.8V_{CC2}		V_{CC2}	V
		P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P14_0, P14_1, XIN, RESET, CNVSS, BYTE	0.8V_{CC1}		V_{CC1}	V
		P7_0, P7_1	0.8V_{CC1}		6.5	V
V_{IL}	LOW Input Voltage (4)	P3_1 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P12_0 to P12_7, P13_0 to P13_7	0		0.2V_{CC2}	V
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 (during single-chip mode)	0		0.2V_{CC2}	V
		P6_0 to P6_7, P7_0 to P7_7, P8_0 to P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P14_0, P14_1, XIN, RESET, CNVSS, BYTE	0		0.2Vcc	V
$I_{OH(peak)}$	HIGH Peak Output Current (4)	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P12_0 to P12_7, P13_0 to P13_7, P14_0, P14_1			–10.0	mA
$I_{OH(avg)}$	HIGH Average Output Current (4)	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P12_0 to P12_7, P13_0 to P13_7, P14_0, P14_1			–5.0	mA
$I_{OL(peak)}$	LOW Peak Output Current (4)	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_0 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P12_0 to P12_7, P13_0 to P13_7, P14_0, P14_1			10.0	mA
$I_{OL(avg)}$	LOW Average Output Current (4)	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_0 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P12_0 to P12_7, P13_0 to P13_7, P14_0, P14_1			5.0	mA
f(XIN)	Main Clock Input Oscillation Frequency	V_{CC1}=4.0V to 5.5V	0		16	MHz
f(XCIN)	Sub-Clock Oscillation Frequency			32.768	50	kHz
f(Ring)	On-chip Oscillation Frequency		0.5	1	2	MHz
f(PLL)	PLL Clock Oscillation Frequency	V_{CC1}=4.0V to 5.5V	10		24	MHz
f(BCLK)	CPU Operation Clock		0		24	MHz
t_{SU}(PLL)	PLL Frequency Synthesizer Stabilization Wait Time	V_{CC1}=5.5V			20	ms

NOTES:

1. Referenced to V_{CC1} = V_{CC2} = 4.7 to 5.5V at T_{opr} = –40 to 85°C / –40 to 125°C unless otherwise specified.
   T version = –40 to 85 °C, V version= –40 to 125 °C.
2. The Average Output Current is the mean value within 100ms.
3. The total $I_{OL(peak)}$ for ports P0, P1, P2, P8_6, P8_7, P9, P10 P1, P14_0 and P14_1 must be 80mA max. The total $I_{OL(peak)}$ for ports P3, P4, P5, P6, P7, P8_0 to P8_4, P12, and P13 must be 80mA max. The total $I_{OH(peak)}$ for ports P0, P1, and P2 must be –40mA max. The total $I_{OH(peak)}$ for ports P3, P4, P5, P12, and P13 must be –40mA max. The total $I_{OH(peak)}$ for ports P6, P7, and P8_0 to P8_4 must be –40mA max. The total $I_{OH(peak)}$ for ports P8_6, P8_7, P9 , P10, P11, P14_0, and P14_1 must be –40mA max.
   As for 80-pin version, the total $I_{OL(peak)}$ for all ports and $I_{OH(peak)}$ must be 80mA. max. due to one V_{CC} and one V_{SS}.
4. There is no external connections for port P1_0 to P1_7, P4_4 to P4_7, P7_2 to P7_5 and P9_1 in 80-pin version.

Table 5.51 A/D Conversion Characteristics (1)

Symbol	Parameter		Measuring Condition		Standard			Unit
					Min.	Typ.	Max.	
–	Resolution		$V_{REF}=V_{CC1}$				10	Bits
INL	Integral Non-Linearity Error	10bit	$V_{REF}=V_{CC1}=5V$	AN0 to AN7 input, AN0_0 to AN0_7 input, AN2_0 to AN2_7 input, ANEX0, ANEX1 input			±3	LSB
				External operation amp connection mode			±7	LSB
		8bit	$V_{REF}=V_{CC1}=5V$				±2	LSB
–	Absolute Accuracy	10bit	$V_{REF}=V_{CC1}=5V$	AN0 to AN7 input, AN0_0 to AN0_7 input, AN2_0 to AN2_7 input, ANEX0, ANEX1 input			±3	LSB
				External operation amp connection mode			±7	LSB
		8bit	$V_{REF}=V_{CC1}=5V$				±2	LSB
–	Tolerance Level Impedance					3		kΩ
DNL	Differential Non-Linearity Error						±1	LSB
–	Offset Error						±3	LSB
–	Gain Error						±3	LSB
R_{LADDER}	Ladder Resistance		$V_{REF}=V_{CC1}$		10		40	kΩ
t_{CONV}	10-bit Conversion Time, Sample & Hold Function Available		$V_{REF}=V_{CC1}=5V$, ϕAD=12MHz		2.75			µs
t_{CONV}	8-bit Conversion Time, Sample & Hold Function Available		$V_{REF}=V_{CC1}=5V$, ϕAD=12MHz		2.33			µs
t_{SAMP}	Sampling Time				0.25			µs
V_{REF}	Reference Voltage				2.0		V_{CC1}	V
V_{IA}	Analog Input Voltage				0		V_{REF}	V

NOTES:
1. Referenced to $V_{CC1}=AV_{CC}=V_{REF}=4.0$ to 5.5V, $V_{SS}=AV_{SS}=0V$ at T_{opr} = –40 to 85°C / –40 to 125°C unless otherwise specified. T version = –40 to 85°C, V version =–40 to 125°C
2. ϕAD frequency must be 12 MHz or less.
3. When sample & hold is disabled, ϕAD frequency must be 250 kHz or more, in addition to the limitation in Note 2. When sample & hold is enabled, ϕAD frequency must be 1MHz or more, in addition to the limitation in Note 2.

Table 5.52 D/A Conversion Characteristics (1)

Symbol	Parameter	Measuring Condition	Standard			Unit
			Min.	Typ.	Max.	
–	Resolution				8	Bits
–	Absolute Accuracy				1.0	%
t_{SU}	Setup Time				3	µs
R_O	Output Resistance		4	10	20	kΩ
I_{VREF}	Reference Power Supply Input Current	(NOTE 2)			1.5	mA

NOTES:
1. Referenced to $V_{CC1}=V_{REF}=4.0$ to 5.5V, $V_{SS}=AV_{SS}=0V$ at T_{opr} = –40 to 85°C / –40 to 125°C unless otherwise specified. T version = –40 to 85°C, V version =–40 to 125°C
2. This applies when using one D/A converter, with the D/A register for the unused D/A converter set to “00h”. The resistor ladder of the A/D converter is not included. Also, when D/A register contents are not “00h”, the I_{VREF} will flow even if Vref id disconnected by the A/D control register.

Table 5.53 Flash Memory Version Electrical Characteristics (1) for 100 cycle products (B, U)

Symbol	Parameter		Standard			Unit
			Min.	Typ.	Max.	
–	Program and Erase Endurance (3)		100			cycle
–	Word Program Time (V_{CC1}=5.0V)			25	200	µs
–	Lock Bit Program Time			25	200	µs
–	Block Erase Time (V_{CC1}=5.0V)	4-Kbyte block	4	0.3	4	s
–		8-Kbyte block		0.3	4	s
–		32-Kbyte block		0.5	4	s
–		64-Kbyte block		0.8	4	s
–	Erase All Unlocked Blocks Time (2)				4×n	s
t_{PS}	Flash Memory Circuit Stabilization Wait Time				15	µs
–	Data Hold Time (5)		20			year

Table 5.54 Flash Memory Version Electrical Characteristics (6) for 10,000 cycle products (B7, U7) (Block A and Block 1 (7))

Symbol	Parameter		Standard			Unit
			Min.	Typ.	Max.	
–	Program and Erase Endurance (3, 8, 9)		10,000 (4)			cycle
–	Word Program Time (V_{CC}1=5.0V)			25		µs
–	Lock Bit Program Time			25		µs
–	Block Erase Time (V_{CC1}=5.0V)	4-Kbyte block	4	0.3		s
t_{PS}	Flash Memory Circuit Stabilization Wait Time				15	µs
–	Data Hold Time (5)		20			year

NOTES:
1. Referenced to V_{CC1}=4.5 to 5.5V at T_{opr} = 0 to 60 °C unless otherwise specified.
2. n denotes the number of block erases.
3. Program and Erase Endurance refers to the number of times a block erase can be performed.
   If the program and erase endurance is n (n=100, 1,000, or 10,000), each block can be erased n times.
   For example, if a 4 Kbytes block A is erased after writing 1 word data 2,048 times, each to a different address, this counts as one program and erase endurance. Data cannot be written to the same address more than once without erasing the block. (Rewrite prohibited)
4. Maximum number of E/W cycles for which operation is guaranteed.
5. Ta (ambient temperature)=55 °C. As to the data hold time except Ta=55 °C, please contact Renesas Technology Corp. or an authorized Renesas Technology Corp. product distributor.
6. Referenced to V_{CC1} = 4.5 to 5.5V at T_{opr} = –40 to 85 °C (B7, U7 (T version)) / –40 to 125 °C (B7, U7 (V version)) unless otherwise specified.
7. Table 5.54 applies for block A or block 1 program and erase endurance > 1,000. Otherwise, use Table 5.53.
8. To reduce the number of program and erase endurance when working with systems requiring numerous rewrites, write to unused word addresses within the block instead of rewrite. Erase block only after all possible addresses are used. For example, an 8-word program can be written 256 times maximum before erase becomes necessary.
   Maintaining an equal number of erasure between block A and block 1 will also improve efficiency. It is important to track the total number of times erasure is used.
9. Should erase error occur during block erase, attempt to execute clear status register command, then block erase command at least three times until erase error disappears.
10. Set the PM17 bit in the PM1 register to “1” (wait state) when executing more than 100 times rewrites (B7 and U7).
11. Customers desiring E/W failure rate information should contact their Renesas technical support representative.

Table 5.55 Flash Memory Version Program/Erase Voltage and Read Operation Voltage Characteristics (at T_{opr} = 0 to 60 °C(B, U), T_{opr} = –40 to 85 °C (B7, U7 (T version)) / –40 to 125 °C (B7, U7 (V version))

Flash Program, Erase Voltage	Flash Read Operation Voltage
V_{CC1} = 5.0 V ± 0.5 V	V_{CC1}=4.0 to 5.5 V

Table 5.56 Power Supply Circuit Timing Characteristics

Symbol	Parameter	Measuring Condition	Standard			Unit
			Min.	Typ.	Max.	
$t_{d(P-R)}$	Time for Internal Power Supply Stabilization During Powering-On	V_{CC1}=4.0V to 5.5V			2	ms
$t_{d(R-S)}$	STOP Release Time				150	µs
$t_{d(W-S)}$	Low Power Dissipation Mode Wait Mode Release Time				150	µs

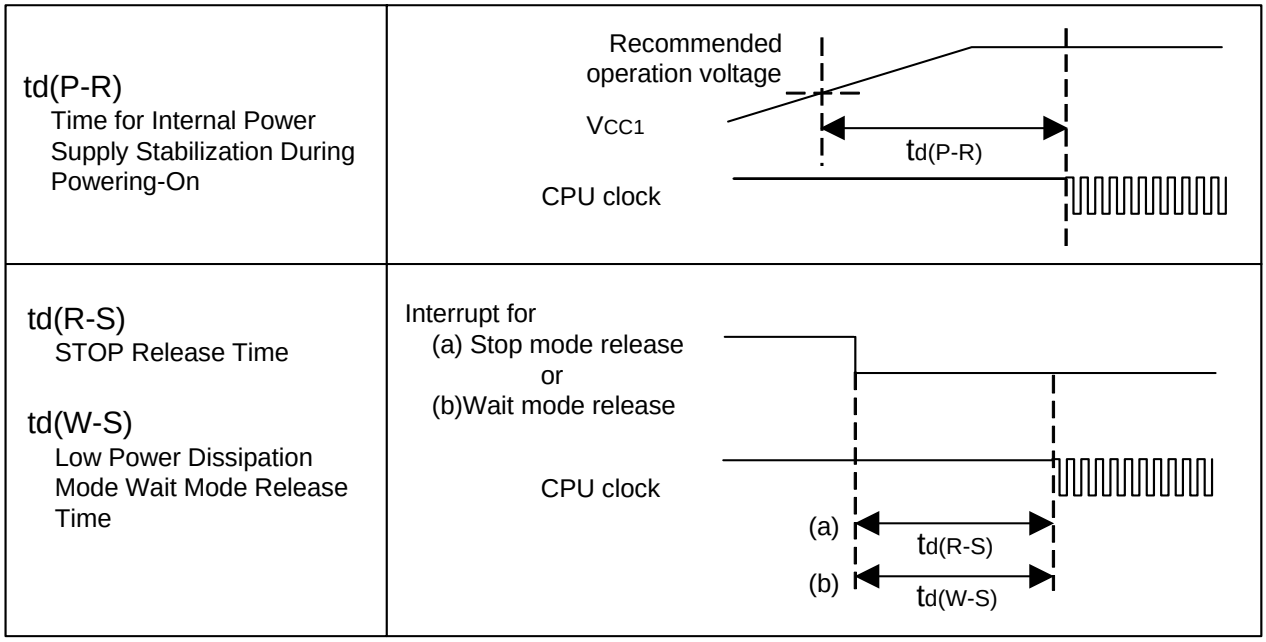


Figure 5.22 Power Supply Circuit Timing Diagram

$V_{CC1}=V_{CC2}=5V$

Timing Requirements
(V_{CC1} = V_{CC2} = 5V, V_{SS} = 0V, at T_{opr} = –40 to 85°C (T version) / –40 to 125°C (V version) unless otherwise specified)

Table 5.59 External Clock Input (XIN input)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
t_c	External Clock Input Cycle Time	62.5		ns
$t_{w(H)}$	External Clock Input HIGH Pulse Width	25		ns
$t_{w(L)}$	External Clock Input LOW Pulse Width	25		ns
t_r	External Clock Rise Time		15	ns
t_f	External Clock Fall Time		15	ns

Rev.	Date	Description	
		Page	Summary
		47	Figure 5.1 Power Supply Circuit Timing Diagram is partly revised.
		48	Table 5.11 Electrical Characteristics (1) is partly deleted.
		49	Table 5.12 Electrical Characteristics (2) is partly revised.
		50	Note 1 of Table 5.13 External Clock Input (XIN input) is added.
		67	Notes 1 to 4 of Table 5.32 External Clock Input (XIN input) are added.
		85	Table 5.53 Flash Memory Version Electrical Characteristics for 100 cycle products is partly revised. Standard (Min.) is partly revised. Table 5.54 Flash Memory Version Electrical Characteristics for 10,000 cycle products is partly revised. Standard (Min.) is partly revised. Note 5 is revised. Table 23.55 Flash Memory Version Program / Erase Voltage and Read Operation Voltage Characteristics is partly revised.
		87	Table 5.57 Electrical Characteristics (1) is partly deleted.
		88	Table 5.58 Electrical Characteristics is partly revised.

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